

MANUFACTURE OF SEMICONDUCTOR DEVICE

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PURPOSE: To prevent next CVD film formation work from a bad influence to be caused by unstable gas of reaction gas at manufacture of a semiconductor device according to the vacuum CVD method by a method wherein a work preliminary process to heat the inside of an empty reaction chamber for the prescribed hours at the high temperature of the prescribed CVD method reaction temperature or more is added in the desired work cycle

CONSTITUTION: Semiconductor wafers 9 accommodated in a decompressed reaction chamber 1 are heated up to the prescribed temperature by an outside heating means 8, and reaction gas 7 is supplied into the reaction chamber to grow the desired growth films on the semiconductor wafers 9. After one time work thereof as usual is completed, a door 2 is opened, the semiconductor wafers 9 completed with the process are taken out together with a boat 10, and the door 2 is closed. After then, the inside of the core tube 1 is decompressed (the same with CVD time or the grade of lower pressure), and heated at a high temperature for the prescribed hours by a heating source 8. Unstable gas of reaction gas in the core tube 1 is reduced or thermally decompressed to a stable material during the holding hours at the high temperature thereof.

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